

Large tunable Josephson diode effect in a side-contacted topological-insulator-nanowire junction

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A Josephson diode passes current with zero resistance in one direction but is resistive in the other direction. While such an effect has been observed in several platforms, a large and tunable Josephson diode effect has been rare. Here we report that a simple device consisting of a topological-insulator (TI) nanowire side-contacted by superconductors to form a lateral Josephson junction presents a large diode effect with the efficiency η reaching 0.3 when a parallel magnetic field B_{\parallel} is applied. Interestingly, the sign and the magnitude of η is found to be tunable not only by B_{\parallel} but also by the back-gate voltage. This novel diode effect can be understood by modeling the system as a nano-SQUID, in which the top and bottom surfaces of the TI nanowire each form a line junction and B_{\parallel} creates a magnetic flux to thread the SQUID loop. This model further shows that the observed diode effect is accompanied by the

emergence of topological superconductivity in TI nanowire based Josephson junction.

1 Introduction

Superconducting (SC) diode effects have recently attracted significant attention^{1,2}, mainly because they allow for the realization of novel SC circuit components for low-dissipation electronics with potential applications in quantum computing^{3,4} and superconducting neural networks⁵. Both bulk superconductors and Josephson junctions may present a diode effect when inversion and time-reversal symmetries are broken, and the latter is called Josephson diode effect². A wide range of mechanisms can give rise to a SC diode effect, including asymmetric vortex pinning in a bulk SC slab⁶⁻⁸, Meissner screening⁹, asymmetric current-phase relationship in a junction¹⁰⁻¹³, magnetochiral anisotropy^{1,14,15}, finite-momentum pairing¹⁶⁻¹⁹, and topological phase transitions²⁰⁻²².

The Josephson diode effect is of particular interest because of its potential for high controllability¹³. One way to achieve a highly tunable device with a high diode efficiency is to make an asymmetric Superconducting Quantum Interference Device (SQUID) involving two or more Josephson junctions^{11,12}. We have recently discovered²³ that a single Josephson junction consisting of a topological-insulator (TI) nanowire side-contacted by two SC electrodes on both sides presents pronounced oscillations of the critical current I_c as a function of the magnetic field B_{\parallel} applied parallel to the nanowire axis, resulting in an $I_c(B_{\parallel})$ behavior akin to a SQUID. Importantly, the period in B_{\parallel} corresponds to the magnetic flux $\Phi_0 = h/2e$, the SC flux quantum, threading the TI nanowire. These results strongly suggest that the side-contacted TI-nanowire junction forms an intrinsic nano-SQUID, where the top and bottom surfaces of the nanowire effectively work as

two parallel SC-normal-SC (SNS) junctions, while the bulk is insulating; the threading magnetic flux Φ imposes a SC phase difference between the two SNS junctions, leading to the I_c oscillations. Therefore, it is interesting to determine if such a nano-SQUID formed intrinsically in a TI-nanowire junction would present a Josephson diode effect, as in other asymmetric SQUIDs¹⁰⁻¹². If it does, such a diode has the potential advantage of being highly tunable by both the parallel magnetic field B_{\parallel} and the back-gate gate voltage V_G , which introduce time-reversal and inversion symmetry breaking, respectively.

In this paper, we demonstrate that the side-contacted TI-nanowire junction indeed presents a large and tunable Josephson diode effect. Intriguingly, the diode efficiency η changes sign with both B_{\parallel} and the back-gate voltage V_G , and its magnitude reaches 0.3 which is comparable to the largest reported for single Josephson junctions¹⁵ without vortex trapping. Our devices are based on TI nanowires with 1 – 2 μm length, 10 – 20 nm thickness, and 60 – 80 nm width, dry-etched from an exfoliated flake of the bulk-insulating TI material BiSbTeSe₂ and side-contacted by Nb electrodes. This structure allows for efficient back-gating, which tunes the asymmetry between the two SQUID arms, an essential ingredient of the Josephson diode effect in the SQUID configuration¹¹. The interface between the TI and Nb has been reported to be sufficiently transparent to give rise to a highly skewed current-phase relationship²⁴, which is also crucial for the Josephson diode effect¹¹. In fact, the spin-momentum locking in the TI surface state guarantees a perfectly-transmitted Andreev mode^{25,26}. Our full three-dimensional simulations of the TI nanowire side-contacted by a conventional superconductor reproduce all the key features observed experimentally, giving confidence in the nano-SQUID origin of the Josephson diode effect. Moreover, our theoretical analysis

shows that the sign change in η corresponds to a topological phase transition in the TI nanowire, which should be accompanied by the emergence of Majorana zero-modes²³. Hence, the relatively simple platform reported here is interesting not only for future SC electronics but also for Majorana physics.

2 Josephson diode effect in a side-contacted TI nanowire junction

Figure 1a shows a false-color scanning-electron microscope (SEM) image of our device A, including the schematics of the pseudo-four-terminal measurement. The Nb electrodes had the transition temperature $T_c \approx 7$ K, and the in-plane upper critical field $H_{c2,\parallel}$ was slightly above 6 T, which was the highest magnetic field available in this experiment. As described in Ref. 23, the precise alignment of the parallel magnetic field B_{\parallel} using a vector magnet was crucial for this type of device. Even a small B_z component will cause the ordinary Fraunhofer interference effect and reduce the I_c , messing up the $I_c(B_{\parallel})$ behavior. We show in Fig. 1c an example of the Fraunhofer pattern measured as a function of B_z in the presence of $B_{\parallel} = 2.2$ T, where one can see that B_z of just a few mT reduces I_c significantly (the asymmetry in the pattern in Fig. 1c is due an anomalous phase created by B_{\parallel} ²⁷). In the following, we focus on results obtained from device A (shown in Fig. 1a), and additional data from three more devices are shown in the supplement. Unless otherwise noted, the data were acquired at the base temperature of our dry dilution refrigerator (≈ 30 mK).

In Fig. 1b, we show the I - V characteristics measured at $B_{\parallel} = -2.5$ T and $V_G = 20$ V to present the Josephson diode effect: The data for positive current I^+ are shown in red, while the data for negative current I^- are shown in blue and are plotted for $|I^-|$ with flipped voltage. In these

measurements, we always swept the current from zero to avoid hysteresis or other complications. The data in Fig. 1b show the critical currents $I_c^+ = 250$ nA and $|I_c^-| = 390$ nA, giving the diode efficiency $\eta \equiv (I_c^+ - |I_c^-|)/(I_c^+ + |I_c^-|) \approx -0.23$. Figure 1d maps the differential resistance dV/dI measured across the junction as a function of B_{\parallel} and the bias current I_b taken at $V_G = 20$ V (white arrows indicate the sweep direction of the bias current); the dark area corresponds to zero resistance and its boundary marks I_c . The pronounced oscillations of I_c as a function of B_{\parallel} having the periodicity of $\Phi_0 (= h/2e)$ is due to the intrinsic nano-SQUID formed in our junction²³.

One can see in Fig. 1d that for most of the B_{\parallel} values, $|I_c^+|$ and $|I_c^-|$ are not the same. This is particularly clear in the region near the I_c -minima (e.g. around $B_{\parallel} \approx 2$ T). Interestingly, across the I_c -minima, the sign of η changes, as highlighted by orange and blue arrows. This sign change is more clearly demonstrated in Fig. 1e, where the B_{\parallel} -dependencies of I_c^+ and $|I_c^-|$ are plotted in red and blue, respectively; here, the critical currents are approximated by the I_b value at which dV/dI exceeded 50Ω . The crossing of $I_c^+(B)$ and $|I_c^-(B)|$ at $B_{\parallel} \approx 2$ T corresponds to the sign change in η .

3 Gate-tunability of the Josephson diode effect

In our TI-nanowire junction, one can tune the sign and the magnitude of the diode effect not only with B_{\parallel} but also with V_G . In Fig. 2a we plot $I_c^+ - |I_c^-|$ as a function of B_{\parallel} and V_G as a color map, where the white color corresponds to zero (i.e. no diode effect). One can see that the diode effect oscillates with B_{\parallel} , resulting in alternation of red and blue; the magnitude of $I_c^+ - |I_c^-|$ can exceed 200 nA at positive V_G , which is large since $|I_c| \lesssim 1 \mu\text{A}$ at all times (see Fig. 1d). Notice that $I_c^+ - |I_c^-|$ is essentially antisymmetric in B_{\parallel} , as expected.

Importantly, we observed that for $|B_{\parallel}| \lesssim 3$ T and at $|B_{\parallel}| \approx 6$ T, the nonreciprocity $I_c^+ - |I_c^-|$ presents a gate-induced sign change. To make this behavior clear, we plot the V_G -dependencies of I_c^+ and $|I_c^-|$ in red and blue lines, respectively, for $B_{\parallel} = 0, -1.8,$ and -2.5 T in Figs. 2b-d. One can see that the two lines cross at -5 V $\lesssim V_G \lesssim 0$ V in $B_{\parallel} = -1.8$ and -2.5 T, while they are essentially indistinguishable at 0 T. One can also notice that the way the sign change occurs is opposite between $B_{\parallel} = -1.8$ and -2.5 T; namely, η ($\propto I_c^+ - |I_c^-|$) changes from negative to positive with increasing V_G in $B_{\parallel} = -1.8$ T, while it is opposite in $B_{\parallel} = -2.5$ T. To further visualize the V_G -induced sign change, in Fig. 2e we plot η in $B_{\parallel} = -1.8$ and -2.5 T as a function of V_G , where the peculiar sign-changing behavior is apparent. Note that $|\eta|$ reaches 0.3 which is large^{2, 11–13, 22, 28}. Figure 3 depicts the parameter regime where this large diode effect is observed; one can see that $|\eta| \approx 0.3$ is achieved near $B_{\parallel} \approx \pm 2$ T where the sign change of $|\eta|$ takes place.

To demonstrate the rectification behavior resulting from our Josephson diode, we performed simple time-domain measurements using another junction, device B: We recorded the voltage waveform when a simple sinusoidal AC current was applied to the junction. In $B_{\parallel} = 1.6$ T, as shown in Fig. 4a, when the AC-current amplitude is ~ 3 μ A (which is larger than $|I_c^-|$ but smaller than $|I_c^+|$), the junction presents a rectified waveform with only negative voltage appearing for negative current. In $B_{\parallel} = 4.3$ T, on the other hand, the sign change in η results in the opposite rectification as shown in Fig. 4b. This experiment demonstrates that the diode polarity is easily switched by the magnetic field. One can similarly switch the diode polarity with gate voltage.

4 Theoretical analysis and simulations

The behavior of the Josephson junction can be modeled phenomenologically as a nano-SQUID where the supercurrent is carried separately by the top and bottom surfaces with skewed current-phase relations,

$$I_\rho(\theta_\rho) = I_{0,\rho} \left[\sin(\theta_\rho) + S_\rho \sin(2\theta_\rho) \right], \quad (1)$$

where $I_{0,\rho}$ and S_ρ determine the magnitude and the skewness of the current-phase relation, and θ_ρ is the superconducting phase difference at the top and bottom surfaces ($\rho = t, b$). The total Josephson current is $I(\theta) = \sum_{\rho=t,b} I_\rho(\theta_\rho)$. The magnetic flux Φ threading through the TI nanowire dictates $\theta_t - \theta_b = 2\pi \frac{\Phi}{\Phi_0} \equiv \phi$. The area that determines Φ in the nano-SQUID model is affected by the localization depth of the TI surface states below the nominal surface, as well as the London penetration depth of the superconductor. The sign of S_ρ determines the skewness direction. Skewed current-phase relations arise naturally in high-transparency Josephson junctions and are right skewed ($S_\rho < 0$)^{29,30}, and intermediate transparency leads to $|S_\rho| \ll 1$; a direct measurement of the current-phase relation for the same TI material was reported in Ref. 24.

A Josephson diode effect in our TI-based nano-SQUID occurs under the following conditions: (i) A magnetic flux through the nanowire breaking time-reversal symmetry, (ii) an asymmetry between the top and bottom surfaces, $I_{0,t} \neq I_{0,b}$ and/or $S_t \neq S_b$, which breaks inversion symmetry³¹⁻³³, and (iii) a finite skewness of the current-phase relation $|S_\rho| > 0$. Time-reversal and inversion symmetry must be broken because their action reverts the direction of current flow. The skewness $|S_\rho| > 0$ ensures the presence of higher harmonics in the current-phase relation that are necessary for the critical currents in opposite directions to be distinct. Conversely, for zero

skewness both individual and total current-phase relations are sinusoidal so that in this case the critical currents in both directions are equal. While the nonreciprocal transport and a SC diode effect have both been discussed for TI nanowires with the current flowing along the wire axis^{32,33}, in the present nano-SQUID setup the current runs perpendicular to the wire axis.

We further performed a full three-dimensional numerical simulation of a TI-nanowire Josephson junction using a tight-binding model (details presented in Methods). The comparison between the simulation results and the relevant experimental data for the critical currents I_c^+ and $|I_c^-|$, together with the diode efficiency, is shown in Fig. 5. As the chemical potential is placed within the bulk band gap of the 3D TI, the current is carried only through the top and bottom surfaces of the nanowire, which yields the nano-SQUID picture. The simulation faithfully reproduces the behavior of critical currents as well as the magnitude of the diode effect, exhibiting sign changes of η at $\Phi = \pm\Phi_0/2$. Crucially, the diode effect appears in the calculation only when the asymmetry between the top and bottom surfaces is present.

In the nano-SQUID model, time-reversal symmetry is restored at integer multiples of half a flux quantum, $\Phi = \frac{n}{2}\Phi_0$, $n \in \mathbb{Z}$. As a consequence, the critical current asymmetry must flip when the flux is mirrored around each half flux quantum, $I_{c\pm}(\frac{n}{2}\Phi_0 + \delta\Phi) = -I_{c\pm}(\frac{n}{2}\Phi_0 - \delta\Phi)$. This requires the diode efficiency η to be periodic and odd around each $\Phi = \frac{n}{2}\Phi_0$. This behavior is approximately observed in the microscopic simulation and in the experiments, with deviations originating from additional effects of the magnetic field beyond the flux, such as Zeeman coupling and a suppression of superconductivity in the Nb leads. To complement this microscopic simulation, the behavior of

the diode effect was also calculated from the phenomenological nano-SQUID model [Eq. (1)], reproducing the key features of the experimental data, as shown in Fig. S7 of the supplement.

In a closed system at equilibrium, the superconducting phase difference across the junction must satisfy the condition that current is conserved:

$$I_t(\theta_0 + \phi) = -I_b(\theta_0) .$$

Here, a gauge is chosen to include the effect of the magnetic flux in the phase difference of the top junction (i.e. $\phi = 2\pi\Phi/\Phi_0$). This equation has two or more solutions due to the periodicity of the supercurrent with the superconducting phase difference, but the system selects the solution that minimizes the free energy of the junction, fixing the equilibrium phase bias θ_0 . At zero temperature, the free energy is given by the Josephson energy $E_J = \frac{\hbar}{2e} \int^\theta d\theta' I(\theta')$. As the flux is increased from $\Phi = 0$ to Φ_0 , the gauge-invariant phase difference $\gamma_{t,b} = \theta_{t,b} + e \int \mathbf{A} d\mathbf{l} / \hbar$ on the weaker junction winds from 0 to 2π while the phase difference of the other junction remains close to 0. For small skewness or large asymmetry, this phase winding is continuous. For larger skewness above a critical value set by the asymmetry, the equilibrium phase difference jumps discontinuously at the flux bias $\Phi = \Phi_0/2$ from θ_0 to $\theta_0 + \Delta\theta$ with $\Delta\theta \approx \pi$. This first-order transition is expected for typical skewness of our device. We confirmed this result from calculations for the phenomenological nano-SQUID model, as shown in Fig. S7 in the supplement.

5 Discussions

Now we discuss the relevance of topology in the present experiment. Since our TI-nanowire junction effectively forms a nano-SQUID consisting of two SNS junctions at the top and bottom TI

surfaces, each SNS junction can be in the topological phase with odd fermion parity in its ground state when the phase difference is between π and $3\pi \pmod{4\pi}$ ³⁴. Since we have two SNS junctions, the TI-nanowire junction as a whole is in the topological phase when only one of the two SNS junctions is topological²³; in this case, Majorana zero-modes are expected to show up at the ends of the TI nanowire. It was theoretically shown in Ref. 23 that when the two junctions are asymmetric, this topological phase is realized in equilibrium in the magnetic-flux range of $(n - \frac{1}{2})\Phi_0 < \Phi < (n + \frac{1}{2})\Phi_0$ with odd-integer n .

It is important to note that in this nano-SQUID, both the diode sign-reversal and the topological phase transition are pinned to half flux quanta by a common origin: the restoration of time-reversal symmetry at these magnetic fluxes. Time-reversal symmetry pins the phase differences of the top and bottom Josephson junctions to 0 or π , where the latter is the topological phase transition point of a single junction³⁴. Importantly, the asymmetry between the top and bottom junctions can be controlled by the gate voltage V_G in our setup; the junction having the smaller Josephson energy will experience the phase winding, thereby undergoing the topological transition. Upon exchanging the top-bottom asymmetry by gating, the junction that experiences the $0-\pi$ transition switches, which coincides with the gate-induced sign reversal of the diode effect.

In the experiments to detect the Josephson diode effect, a bias current is passed through the junction and it dictates the phase difference across the junction according to the current-phase relationship. This means that the phase is not a free parameter in the current-biased experiment and the persistence of the topological phase is not guaranteed upon current biasing. It is an interesting

topic of future research to clarify the role of current bias to control the topological phase transition.

In conclusion, we found that the intrinsic nano-SQUID nature of the TI-nanowire junction²³ leads to a large Josephson diode effect, whose size and sign can be tuned by the parallel magnetic field B_{\parallel} and the back-gate voltage V_G . Our theoretical modeling shows that the sign change in the Josephson diode efficiency η as a function of B_{\parallel} is accompanied by a topological phase transition in equilibrium, making the TI-nanowire junction interesting not only for SC electronics but also for studying topological superconductivity and Majorana zero-modes. Moreover, given that other tunable Josephson diodes based on SQUID geometry tend to be large and complicated^{11,12}, the small and simple nature of our device is an advantage for integrating the Josephson diodes in large-scale circuits, although the necessity of a magnetic field can be a limiting factor.

Methods

Materials and device fabrications: Bulk single crystals of BiSbTeSe₂ were grown using the modified Bridgman method, following the procedure outlined in Ref. 35, with high-purity (99.9999%) Bi, Sb, Te, and Se as starting materials. Thin flakes of BiSbTeSe₂ were mechanically exfoliated from a bulk crystal and transferred onto a degenerately-doped Si wafer coated with a 290 nm SiO₂ layer, which acts as a dielectric for the back gate. Flakes suitable for device fabrication were identified under an optical microscope. Nanowires and Josephson junctions were patterned using electron beam lithography, with ZEP 520A resist exposed via a Raith PIONEER Two system. The BiSbTeSe₂ flakes were dry-etched into nanowires using Ar plasma. Subsequently, 45 nm of Nb were sputter-deposited to form the junctions. The device geometry was precisely characterized

using scanning electron microscopy and atomic force microscopy after the completion of measurements.

Measurements: Transport measurements were conducted at the base temperature (~ 30 mK) of our Oxford Instruments TRITON 300 dry dilution refrigerator. To minimize noise, the electrical lines were equipped with RC and copper-powder filters. We utilized a quasi-four-probe configuration to measure the differential resistance dV/dI across the Josephson junction employing a standard low-frequency lock-in technique, where a small AC current of 5 nA was superimposed on a DC bias current. Note that whenever a four-terminal measurement was not possible due to defected leads, a quasi three-probe technique was applied instead (which was the case for device A). To apply magnetic fields, we employed a 6/1/1-T superconducting vector magnet.

Simulations: The proximitized nanowire of three-dimensional topological insulator (3DTI) BiSbSeTe₂ was described using the standard 3D massive Dirac fermion model that is commonly used for materials from Bi₂Te₃ family. The Hamiltonian of the model is given by:

$$\begin{aligned}
H_{\text{TI}}(\mathbf{k}) = & A_1 k_z s_z \sigma_x + A_2 (k_x s_x + k_y s_y) \sigma_x \\
& + (M - B_1 k_z^2 - B_2 (k_x^2 + k_y^2)) s_0 \sigma_z \\
& + (C + D_1 k_z^2 + D_2 (k_x^2 + k_y^2) - \mu_{\text{TI}}) s_0 \sigma_0
\end{aligned} \tag{2}$$

where s_i and σ_i are Pauli matrices describing spin and orbital degrees of freedom, respectively. The niobium superconductor that forms the Josephson junction is described using a simple parabolic band with the Hamiltonian:

$$H_{\text{SC}}(\mathbf{k}) = \left(t(k_x^2 + k_y^2 + k_z^2) - \mu_{\text{SC}} \right) s_0 \sigma_0 \tag{3}$$

Both Hamiltonians are discretized on a cubic lattice with the spacing $a_{\text{lat}} = 1 \text{ nm}$ using the finite difference method with nearest-neighbor hoppings. Since the devices under study are much longer ($L > 1 \mu\text{m}$) than their width or height ($W, H \sim 10 \text{ nm}$), it is assumed that translational invariance is retained in the z direction and thus k_z remains a good quantum number.

After the discretization, both systems are combined in a single real-space Hamiltonian, which is given by:

$$H_0(x) = H_{\text{SC}}\theta(-x) + H_{\text{TI}}(\theta(x) - \theta(W - x)) + H_{\text{SC}}\theta(x - W) \quad (4)$$

where W is the width of the 3DTI nanowire and $\theta(x)$ is the Heaviside step function. We include the effect of magnetic field via the Peierls' substitution, where the hoppings between sites \mathbf{r}_n and \mathbf{r}_m are replaced by:

$$t_{mn} \rightarrow t_{mn} \exp\left(-i\tau_z \frac{e}{\hbar} \int_{\mathbf{r}_n}^{\mathbf{r}_m} d\mathbf{r} \cdot \mathbf{A}(\mathbf{r})\right) \quad (5)$$

where $\tau_z = \pm 1$ for particle and hole degrees of freedom, respectively. In all the calculations we use the gauge where $\mathbf{A}(\mathbf{r}) = -B_z y \hat{x}$. This assumes that the magnetic field penetrates the device fully, which is justified as the thickness of the superconducting electrodes (about 45 nm) is comparable to the London penetration depth of niobium. The flux through the junction is then established as $\Phi = B_z \tilde{A}$, where \tilde{A} is the effective junction area.

To enable the superconducting diode effect, asymmetry between the top and bottom surface state of the nanowire has to be introduced through the gate electrostatic potential, which we model by a gradient of the chemical potential inside of the topological insulator $\mu_{\text{TI}}(y) = \mu_{\text{TI}} + V_g y / H$.

The superconductivity then is treated using Bogoliubov-de Gennes (BdG) Hamiltonian:

$$H_{\text{BdG}} = \begin{pmatrix} H_0(\mathbf{k}) & \Delta \\ \Delta^\dagger & -H_0^T(-\mathbf{k}) \end{pmatrix} \quad (6)$$

where the superconducting order parameter Δ is:

$$\Delta(x) = \Delta_0 (\exp(-i\phi/2)\theta(-x) + \exp(i\phi/2)\theta(x - W)) i s_y \sigma_0 \quad (7)$$

with ϕ being the phase difference between the superconducting condensates.

With such a setup constructed, we then calculate the current-phase relations for varying magnetic field by using the excitation spectrum of the BdG Hamiltonian. The Josephson current density along the quasi-1D nanowire is expressed through the positive eigenvalues that are a function of the momentum component parallel to the nanowire axis:

$$j(\phi) = -\frac{e}{\hbar} \sum_{\epsilon_n > 0} \int \frac{dk_z}{2\pi} \tanh\left(\frac{\epsilon_n(k_z)}{2k_B T}\right) \frac{d\epsilon_n(k_z)}{d\phi} \quad (8)$$

where k_B is the Boltzmann constant and T is the temperature. The integration is performed by discretizing momenta and calculating the spectrum at 281 points for $k_z a_{\text{lat}}$ in the range $[-1.4, 1.4]$. From the supercurrent density the total current through the junction is obtained as $I(\phi) = j(\phi)L$, and then the critical supercurrent in both directions is determined as $I_{c+} = \max(I(\phi))$ and $I_{c-} = \min(I(\phi))$, respectively. In the simulations the parameters are as follows: $a_{\text{lat}} = 1$, $A_1 = 0.25$, $A_2 = 0.35$, $B_1 = -0.3$, $B_2 = -0.6$, $C = 0$, $D_1 = 0.025$, $D_2 = -0.05$, $M = -0.25$, $\mu_{\text{TI}} = 0.0$, $V_g = 0.05$, $t = 1.0$, $\mu_{\text{SC}} = 1.0$, $\Delta_0 = 0.08$, $W = 14$, $W_{\text{SC}} = 16$, $H = 15$, $L = 1500$, with all the energies expressed in eV and all the lengths in nm. The parameters are chosen such that the bulk gap of the 3DTI is in agreement with experimentally determined gap 250-300 meV of BiSbSeTe₂.

These parameters also translate to a topological surface state with a Fermi velocity $v_F \approx 4 \cdot 10^5$ m/s. The imperfect transmission at the superconductor-3DTI interface was modeled via the Fermi wave vector mismatch, which was $k_{F,SC}/k_{F,TI} \approx 4$. To make the simulations numerically tractable the use of lattice discretization with 1 nm spacing required increasing the superconducting gap magnitude from the experimental value of $\Delta_{\text{exp}} \sim 0.9$ meV. The width of the Josephson junction is chosen such that the proximity induced gap in the topological insulator is about 1/2 of the gap of the superconducting electrodes, as was determined in the studied device.

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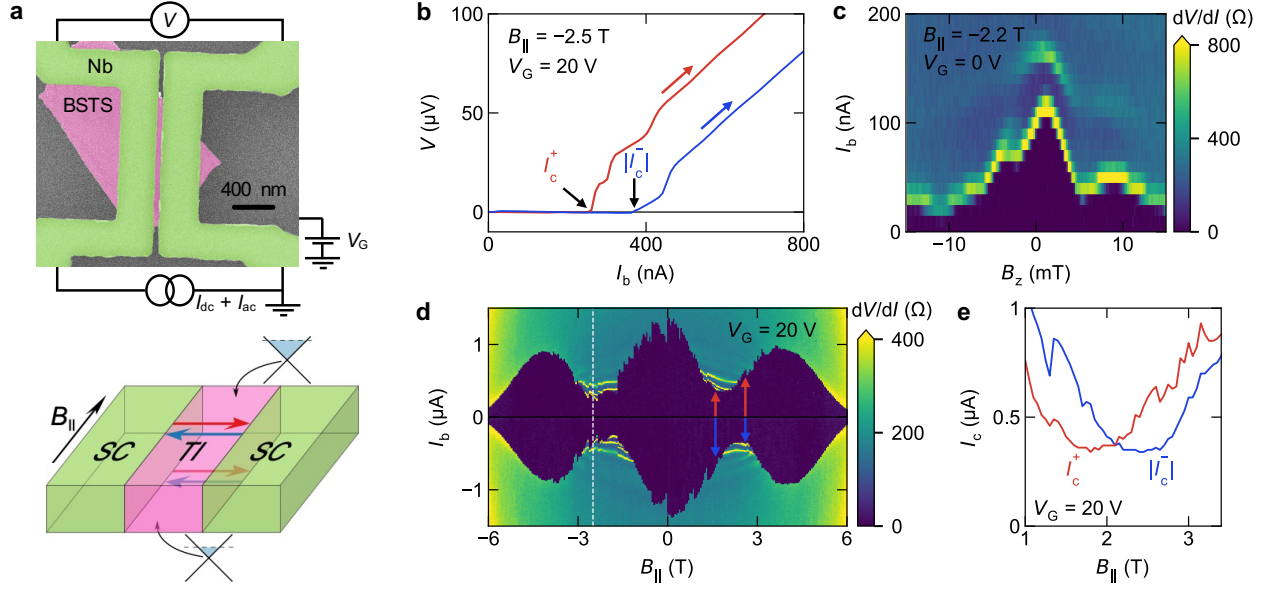


Figure 1: **Device schematics and the behavior of the critical current.** **a**, False-color SEM image of device A with schematics of the pseudo-four-terminal measurement. An exfoliated TI flake is dry-etched into a nanowire (pink). The etched area is filled with Nb (green) to form a sandwich junction. There are remaining TI pieces that do not play any role. The lower drawing shows that the supercurrents flow through the top and bottom topological surface states, whose chemical potentials can be made different by a back-gate; a magnetic field applied parallel to the nanowire axis causes the Josephson diode effect. **b**, I - V characteristics of device A taken at $B_{\parallel} = -2.5$ T and $V_G = 20$ V. For better comparability with the positive bias curve (red), the negative bias curve (blue) was flipped horizontally and vertically. The current sweep was always from zero as indicated by the red and blue arrows. **c**, Color map of dV/dI as function of out-of-plane magnetic field B_z and I_b at $B_{\parallel} = 2.2$ T and $V_G = 0$ V in device A. **d**, Color map of dV/dI as function of B_{\parallel} and I_b at $V_G = 20$ V in device A. White arrows indicate the sweep direction of I_b . Orange and blue arrows highlight the diode effect. The black dashed line mark the B_{\parallel} value where the data in **b** was taken. **e**, Plot of I_c^+ and $|I_c^-|$ extracted from the data in **d** as function of B_{\parallel} near an I_c^- -minimum at $B_{\parallel} \approx 2$ T.

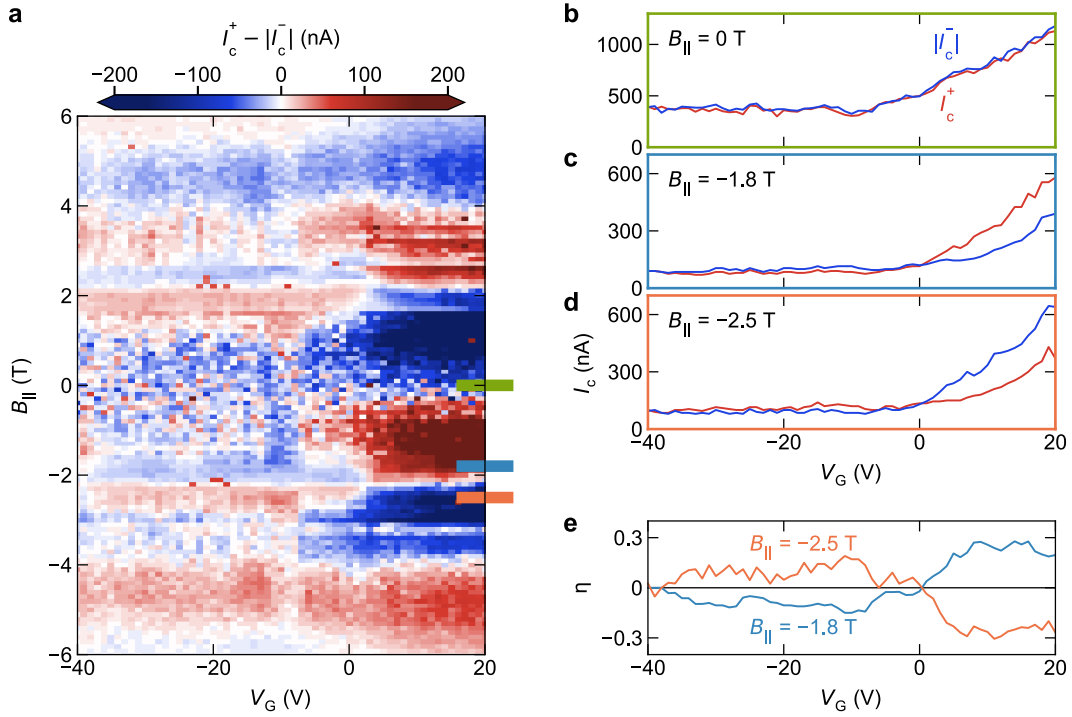


Figure 2: **Tunability of the diode efficiency.** **a**, Color mapping of $I_c^+ - |I_c^-|$ as a function of V_G and $B_{||}$ in device A, demonstrating the tunability of the Josephson diode effect. **b-d**, Raw data of $I_c^+(V_G)$ and $|I_c^-(V_G)|$ used for producing **a** at $B_{||} = 0, -1.8,$ and -2.5 T; these $B_{||}$ values are marked in **a** with corresponding colors. **e**, V_G -dependence of the diode efficiency η for $B_{||} = -1.8$ T and -2.5 T calculated from the data in **c** and **d**.

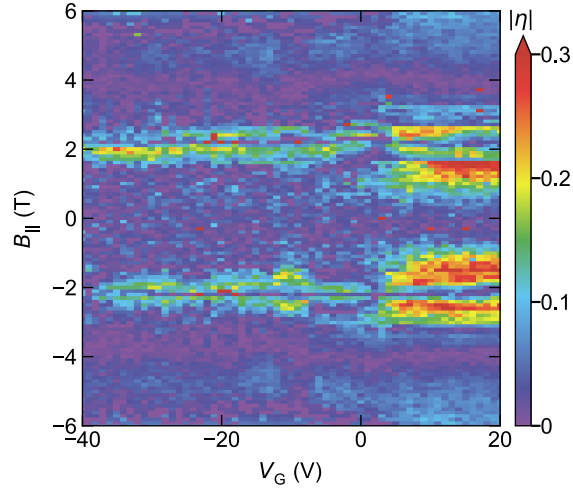


Figure 3: **Magnitude of the diode efficiency.** Color mapping of $|\eta|$ as a function of V_G and $B_{||}$ in device A, showing that the magnitude of the diode efficiency can reach 0.3 near the sign-switching magnetic field $B_{||} \approx \pm 2$ T.

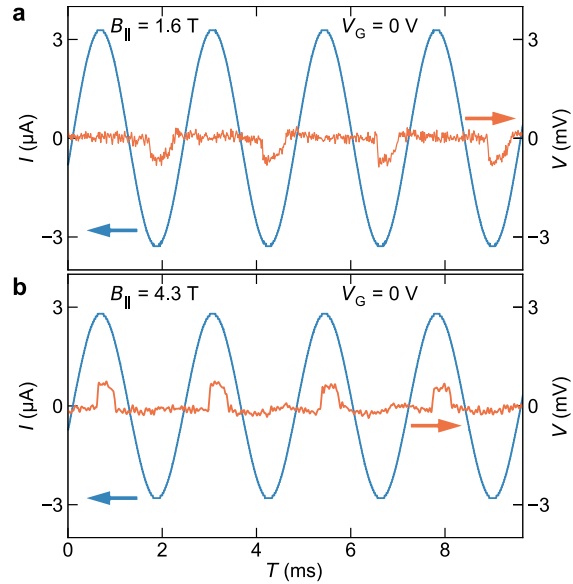


Figure 4: **Visualization of the rectification effect.** **a,b** Time-resolved measurement of the voltage drop across the Josephson junction (orange curve) in response to a sinusoidal AC current with an amplitude of $\sim 3 \mu\text{A}$ (blue), highlighting the rectification effect. The data in **a** and **b** were acquired at $B_{||} = 1.6$ and 4.3 T, respectively, where the sign of η was opposite. The measurement was performed on device B.

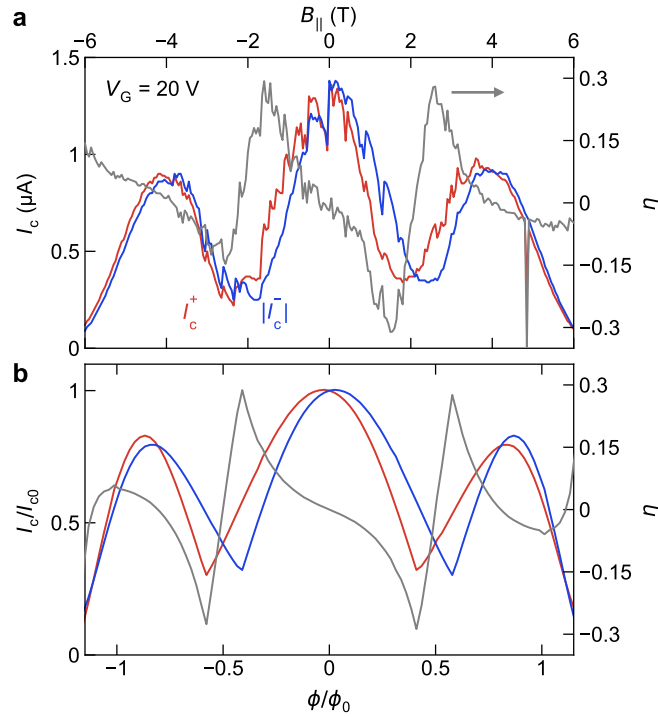


Figure 5: **Comparison with a theoretical simulation.** **a**, Experimental data of the critical currents I_c^+ and $|I_c^-|$ as a function of parallel magnetic field, together with the diode efficiency as measured in device A. **b**, Simulation based on a tight-binding model of a TI nanowire proximitized from both sides by a regular superconductor.

Supplementary information for “Large tunable Josephson diode effect in a side-contacted topological-insulator-nanowire junction”

S1. EXPERIMENTAL DETAILS AND ADDITIONAL DATA

A. Sample geometry

Following the transport measurements, the device geometry was accurately characterized using the scanning electron microscopy (SEM) images shown in Figs. S1a-d to determine the length L and width W of the nanowires. The nanowire thickness was measured using atomic force microscopy (AFM). The geometric parameters for devices A, B, C, and D are summarized in Table S1.

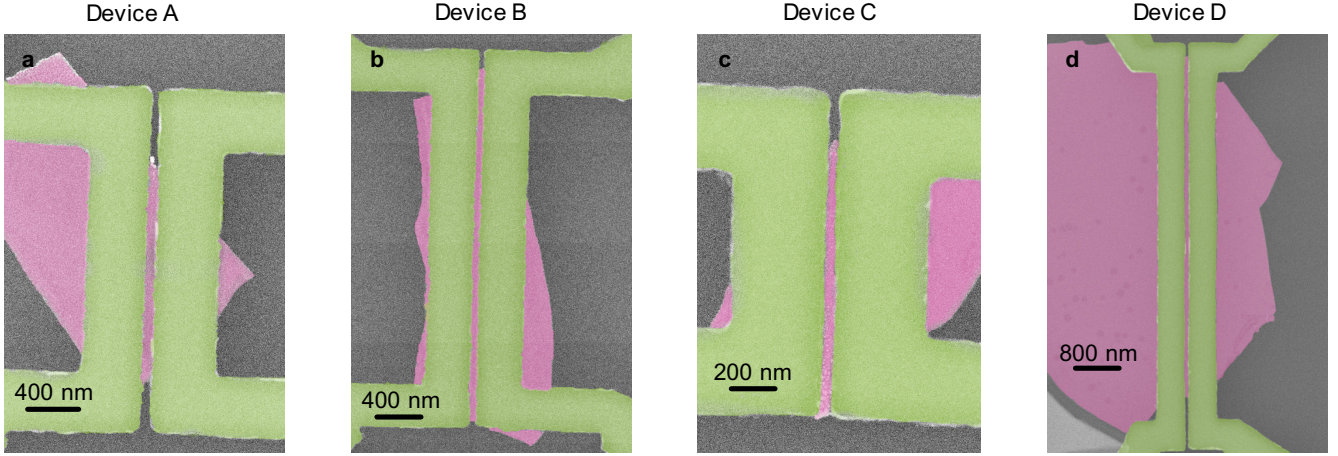


FIG. S1: SEM images of devices A-D.

Device	d (nm)	W (nm)	L (μm)
A	15	60	1.2
B	22	80	2.4
C	13	60	1.5
D	12	70	4.9

TABLE S1: Nanowire dimensions for devices A–D.

B. Magnetic field alignment

The precise alignment of the magnetic field relative to the junction’s coordinate system is crucial for studying the junction properties in magnetic fields parallel to the nanowire axis, B_{\parallel} . Misalignment introduces a nonzero B_z component, leading to phase winding and a current modulation along

the junction, as observed in a Fraunhofer measurement. To achieve good alignment, multiple Fraunhofer-type measurements were performed with intentionally-applied small B_z fields in the presence of large nominal B_{\parallel} fields. These data reveal a systematic shift in the position of the maximum critical current I_c arising from a spurious B_z component caused by misalignment. By identifying the necessary B_z value to compensate the spurious B_z component for each nominal B_{\parallel} , we achieved the necessary alignment of B_{\parallel} . The precise procedure is described in Ref. [1]. On the other hand, a small misalignment of the magnetic field within the device plane from the nanowire axis does not affect the data in any noticeable manner.

C. Reproducibility of the Josephson diode effect

In Figs. S2, S3, S4, we show data for three more devices B, C, and D not presented in the main text. As shown in Fig. S1, the device design is essentially the same as the one discussed in the main text. All key features are reproduced in these devices. In the presence of a finite B_{\parallel} , all of the devices develop a pronounced Josephson diode effect that is periodic in B_{\parallel} . Note that in contrast to devices C and D, device B was not gate-tunable due to an accidental short to the back gate. Intriguingly, in device D we observe two sign changes of the diode efficiency as a function of V_G as shown in Fig. S4d.

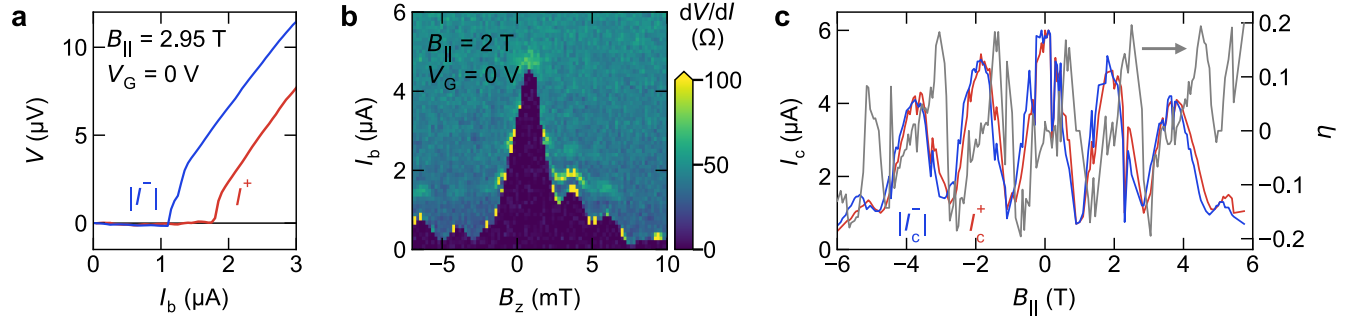


FIG. S2: **Reproducibility in device B.** **a**, I - V characteristics at $B_{\parallel} = 2.95$ T and $V_G = 0$ V. The negative bias curve (blue) was flipped horizontally and vertically. The current sweep was always from zero. **b**, Color map of dV/dI as a function of B_z and I_b at $B_{\parallel} = 2$ T and $V_G = 0$ V. **c**, I_c for positive bias currents (red) and negative bias currents (blue), as well as the diode efficiency η (grey) as a function of B_{\parallel} at $V_G = 0$ V. This device was not gate-tunable. Measurements were at $T = 30$ mK.

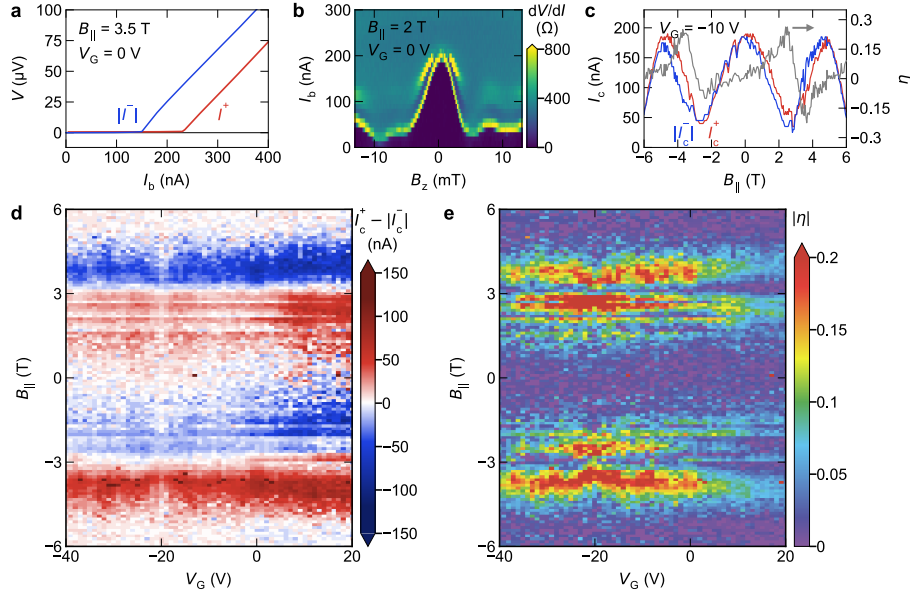


FIG. S3: **Reproducibility in device C.** **a**, I - V characteristics at $B_{\parallel} = 3.5$ T and $V_G = 0$ V. The negative bias curve (blue) was flipped horizontally and vertically. The current sweep was always from zero. **b**, Color map of dV/dI as a function of B_z and I_b at $B_{\parallel} = 2$ T and $V_G = 0$ V. **c**, I_c for positive bias currents (red) and negative bias currents (blue), as well as the diode efficiency η (grey) as a function of B_{\parallel} at $V_G = -10$ V. **d**, Color mapping of $I_c^+ - |I_c^-|$ as a function of V_G and B_{\parallel} . **e**, Color mapping of $|\eta|$ as a function of V_G and B_{\parallel} . Measurements were at $T = 30$ mK.

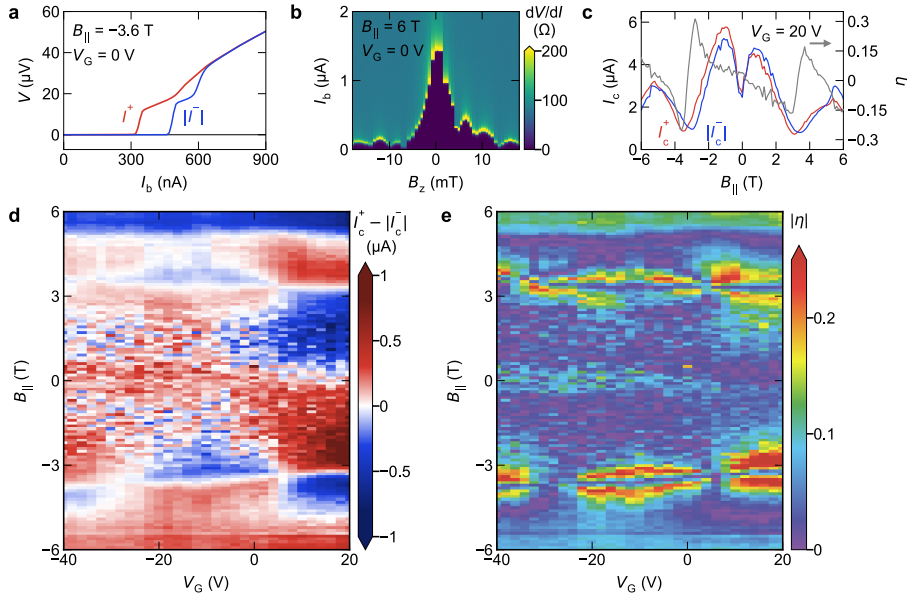


FIG. S4: **Reproducibility in device D.** **a**, I - V characteristics at $B_{\parallel} = -3.6$ T and $V_G = 0$ V. The negative bias curve (blue) was flipped horizontally and vertically. The current sweep was always from zero. **b**, Color map of dV/dI as a function of B_z and I_b at $B_{\parallel} = 6$ T and $V_G = 0$ V. **c**, I_c for positive bias currents (red) and negative bias currents (blue), as well as the diode efficiency η (grey) as a function of B_{\parallel} at $V_G = 20$ V. **d**, Color mapping of $I_c^+ - |I_c^-|$ as a function of V_G and B_{\parallel} . **e**, Color mapping of $|\eta|$ as a function of V_G and B_{\parallel} . Measurements were at $T = 30$ mK.

D. Josephson diode effect at 1 K

Figures S5 and S6 show $I_c^+ - |I_c^-|$ and the diode efficiency $|\eta|$, respectively, as a function of V_G and B_{\parallel} for devices A, C, and D measured at $T = 1$ K. The tunability of $I_c^+ - |I_c^-|$ remains unaffected by the increased temperature, while the magnitude of I_c in both bias directions is slightly reduced. The diode efficiency is largely robust against the temperature increase.

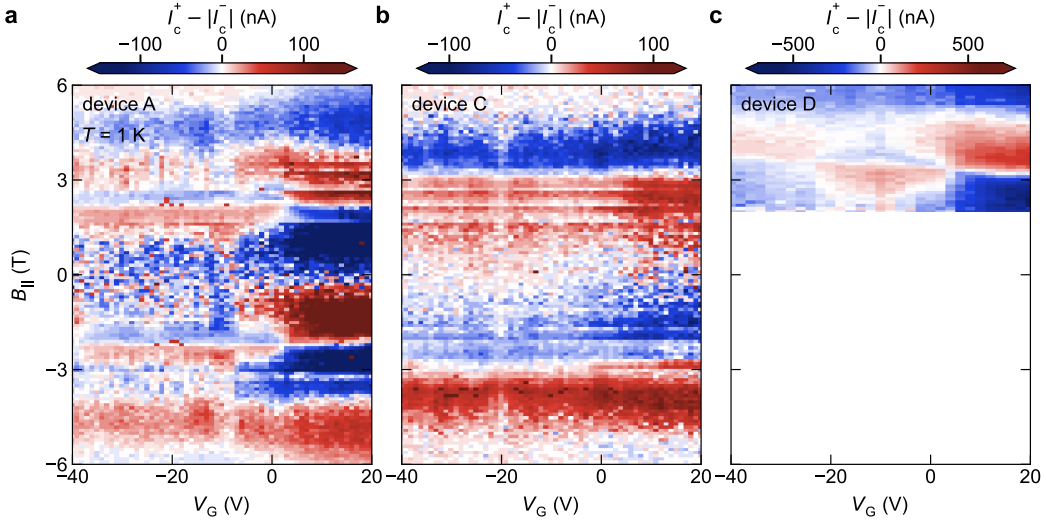


FIG. S5: **a, b, c**, Color mapping of $I_c^+ - |I_c^-|$ at $T = 1$ K as a function of V_G and B_{\parallel} in devices A, C, and D. The measurement of Device D at 1 K was performed only for a limited range of B_{\parallel} , since there was little change from the behavior at 30 mK shown in Fig. S4.

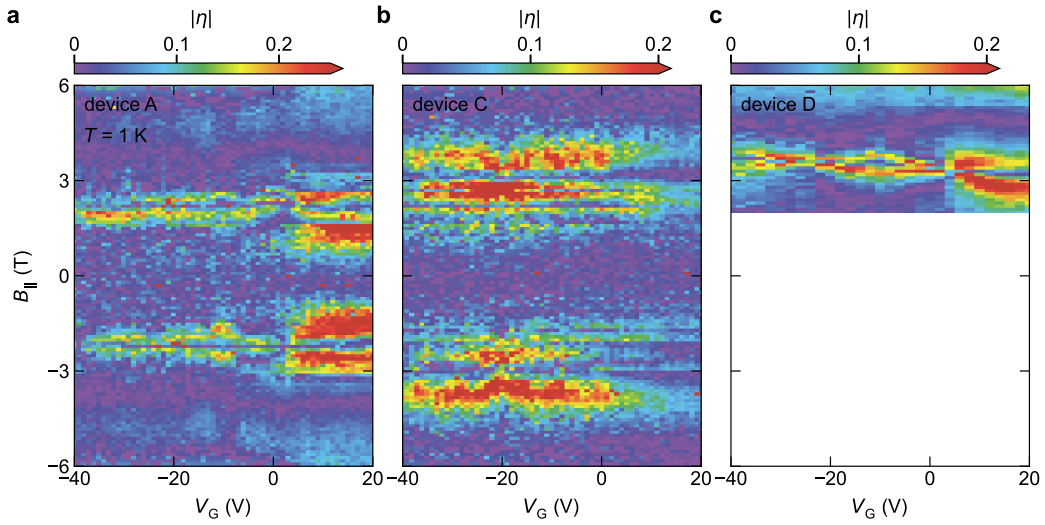


FIG. S6: **a, b, c**, Color mapping of $|\eta|$ at $T = 1$ K as a function of V_G and B_{\parallel} in devices A, C, and D.

S2. MECHANISM OF THE SIGN REVERSAL OF THE DIODE EFFECT

The phenomenological nano-SQUID model, Eq. (1) in the main text, predicts a sign reversal of the diode efficiency at integer multiples of half magnetic flux quanta, see Fig. S7 for results derived from the nano-SQUID model. This is a robust feature of the nano-SQUID description because it is tied to the restoration of time-reversal symmetry at these flux values. Notably, the sign reversal of the diode efficiency is also observed in the experimental data [Fig. 2(a) in the main text] for the whole range of gate voltages at the magnetic field corresponding to the flux $\Phi = \Phi_0/2$. Qualitative agreement of the experimental data with the phenomenological model supports the conclusion that the supercurrent is predominantly carried by the top and bottom surface states separately. Further, we compute the diode efficiency as a function of top-bottom asymmetry $\frac{I_{0,t}-I_{0,b}}{I_{0,t}+I_{0,b}}$ and magnetic flux, with the result shown in Fig. S8. The diode efficiency changes sign around the time-reversal symmetry points $\Phi = \frac{n}{2}\Phi_0$, $n \in \mathbb{Z}$ as well as when the top-bottom asymmetry is exchanged. Already with fixed skewness $S_t = S_b = -0.2$, the diode efficiency approaches the theoretical maximum of $|\eta| = \frac{1}{3}$ that is achievable with current phase-relations containing only first- and second harmonic components [2].

The sign reversal of the diode effect as a function of the gate voltage V_G also appears near $V_G \approx 0$ in the experimental data [Fig. 2(e)] for several magnetic field values. The direction of the diode effect can thus be controlled by the gate voltage V_G , in addition to the magnetic flux that threads the nanowire. Furthermore, for a large positive gate voltage V_G , the experimental diode efficiency approaches the theoretical maximum of $|\eta| = \frac{1}{3}$ mentioned above. While the experimental current-phase relations may contain any order of harmonics, we expect that the second harmonic dominates over the higher harmonics because the long nanowire has many transverse modes for which higher harmonics are suppressed by specular reflection competing with the Andreev reflection at the superconductor interface. This picture is also confirmed by our microscopic simulations, where we observed $|\eta| < 1/3$.

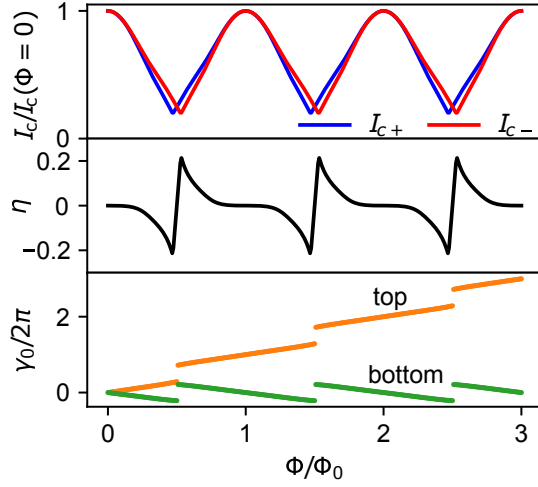


FIG. S7: **Phenomenological model.** Critical currents in positive and negative directions $I_{c\pm}$, diode efficiency η , and gauge-invariant equilibrium phase bias $\gamma_{0,t/b} = \theta_0 + \int \mathbf{A}d\mathbf{l} = \theta_0 \pm \pi\Phi/\Phi_0$ at top- and bottom surface as a function of magnetic flux. Shown here are the model calculations from Eq. (1) in the main text with skewness $S_t = S_b = -0.2$ and asymmetry $I_{0,t}/I_{0,b} = 0.8$.

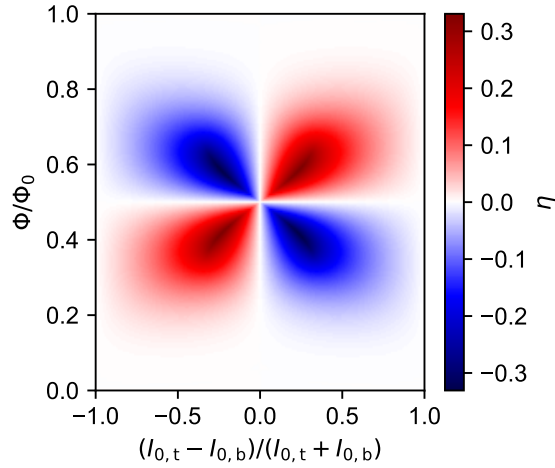


FIG. S8: Diode efficiency calculated from Eq. (1) in the main text, as a function of Φ and top-bottom asymmetry $\frac{I_{0,t} - I_{0,b}}{I_{0,t} + I_{0,b}}$. The skewness parameter setting the weight of the second harmonic is $S_t = S_b = 0.2$.

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- [1] E. Nikodem, J. Schluck, H. F. Legg, M. Geier, M. Papaj, M. Bagchi, L. Fu, and Y. Ando, Topological columnar nano-SQUID based on a 3D topological insulator, arXiv e-prints , arXiv:2412.07993 (2024).
- [2] The theoretical maximum $|\eta| = \frac{1}{3}$ for current-phase relations with first- and second-harmonic components of the form $I_0 (\sin(\theta) + S \sin(2\theta + \delta\theta))$ is reached for $S = 0.5$ and $\delta\theta = \pi/2$.